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Comparative study of defect energetics in HfO_2 and SiO_2

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We perform ab initio calculations, based on density functional theory, of substitutional and vacancy defects in the monoclinic hafnium oxide (m-HfO_2) and -quartz (SiO_2). The neutral oxygen vacancies and substitutional Si and Hf defects in HfO_2 and SiO_2, respectively, are investigated. Our calculations show that, for a large range of Hf chemical potential, Si substitutional defects are most likely to form in HfO_2, leading to the formation of a silicate layer at the HfO_2/Si interface. We also find that it is energetically more favorable to form oxygen vacancies in SiO_2 than in HfO_2, which implies that oxygen deficient HfO_2 grown on top of SiO_2 will consume oxygen from the SiO_2.

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The continuous device miniaturization in the microelectronic industry will eventually lead, within the present technology, to the end of the use of amorphous SiO_2 (a-SiO_2) as gate dielectric in metal-oxide-semiconductor field-effect transistors (MOSFETs). The existence of a thickness limit for the a-SiO_2 around 10–12 A, has clearly been established experimentally [1]. One way to circumvent this problem, still keeping Si as the basic device material, is to employ high-permitivity materials as alternative gate dielectrics in place of the conventional a-SiO_2. Among them, hafnium oxide is emerging as the material with greatest potential to substitute SiO_2, mainly due to its high dieletric constant and thermodynamic stability, when it forms interface with Si.

Even though hafnium oxide is thermodynamically stable against an overall decomposition as Hf and SiO_2 when grown on Si, interfacial reactions can occur. Thereby the formation of a thin interfacial layer (oxides, silicates and silicides) between the HfO_2 and the Si surface, has been recently observed [2, 3]. This interfacial layer occurs during almost any film growth processes or post-annealing, which is an intrinsic part of any growth cycle. Therefore, the thermodynamic stability of the hafnium oxide in contact with silicon is identified as a critical issue for the application of alternative gate dielectric in silicon-based devices [4, 5]. Moreover, the study of possible defects related to the migration of atoms across the interface is of fundamental importance. In particular, a significant source of defects in this system is the interface itself, which has been shown [6] to consist of Hf silicates with dielectric constant lower than that of HfO_2 [7, 8].

In the present work we address the formation of neutral defects through first-principles calculations, based on the density functional theory (DFT). We analyze the formation of Si substitutional defects in HfO_2, as well as Hf substitutional defects in SiO_2, for different growth conditions. Finally, the energetics of an oxygen vacancy in SiO_2 is compared to a similar vacancy in HfO_2, in order to understand the growth of hafnium oxide under oxygen-poor conditions.

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Many experimental works [9, 10, 11, 12] have addressed the chemical reactions that could occur in the HfO_2/Si interface during the HfO_2 growth cycle. This is due in order to prevent and/or control the interfacial layer formation. Almost all works have reported the formation of an interfacial Hf silicate in oxygen-rich atmospheres. Furthermore, Wang and co-workers [13] have shown that in opposite conditions, i.e., oxygen-deficient atmospheres, the Hf silicate interfacial formation does not happen during the HfO_2 growth cycle. However, there are still many open questions, such as which atomic species are migrating when the interfacial silicate is formed. For example, it is important to know if Hf will be incorporated in a formed SiO_2 layer, or if Si from either the bulk Si or this SiO_2 layer will be incorporated in the HfO_2.

The DFT calculations were performed using ultrasoft Vanderbilt pseudopotentials [14], and the generalized gradient approximation (GGA) for the exchange-correlation potential as implemented in VASP code [15, 16, 17, 18]. In order to study the defects in the different systems we have considered the monoclinic HfO_2 and the -quartz (SiO_2) crystalline phases, using a 96 atoms and 72 atoms supercells, respectively. For these cells, we have used a plane wave cutoff energy of 400 eV and a 2 2 2 Monkhorst-Pack k-mesh. These crystal structures have been previously used to describe these systems [19, 20, 21]. In all calculations the atoms were allowed to relax until all components of the atomic forces were smaller than 0.025 eV/A.

The silicon substitutional defect (Si_{Hf}) was created in the m-HfO_2 supercell by substitution of one hafnium atom by one silicon atom in the equilibrium perfect crystal. On the other hand, the hafnium substitutional defect (Hf_{Si}) was created in the -quartz by substitution of one silicon atom by one hafnium atom in the equilibrium perfect crystal. Our results show that the presence of either Si_{Hf} or Hf_{Si} in HfO_2 or SiO_2, respectively, do not introduce any additional active levels in the band gap. For the perfect HfO_2 at the equilibrium, we obtain an indirect band gap of 3.9 eV along -B. For this same supercell, the density of states (DOS) shows that the O (2s) and O (2p) bands are centered at around -14 and 0 eV, with bandwidths of approximately 4 eV and 8 eV, respectively, below valence-band edge, whereas the Hf(5d)

band is centered at around 8 eV forms in the conduction band, with bandwidth of 6 eV. These results are in good agreement with previous DFT calculations of this material [22]. Moreover, for HfO_2 with a Si substitutional defect, we observe a resonant state around 6.9 eV below the top of the valence band, which is related to the O (2p)-like and Si bonding state [23].

The formation energy for a Si_{Hf} is calculated as

$$E_f^{Si_{Hf}} = [E_t(Si_{Hf}) + \mu_{Hf}] - [E_t(HfO_2) + \mu_{Si}]; \quad (1)$$

whereas for Hf_{Si} the similar expression is

$$E_f^{Hf_{Si}} = [E_t(Hf_{Si}) + \mu_{Si}] - [E_t(SiO_2) + \mu_{Hf}]: \quad (2)$$

In the above expressions, $E_t(D_S)$ are the total energies of the fully relaxed supercells (either m-HfO_2 or SiO_2) with the substitutional defect D_S, and $E_t(XO_2)$ are the total energies of the similar supercells for the perfect crystals of XO_2 (X = Hf or Si). The values of the chemical potentials, μ_{Hf} and μ_{Si}, depend on the growth conditions. We have considered two limits for μ_{Hf}: (i) The bulk metal as a reference, which would correspond to a Hf-rich growth condition and the formation of Hf clusters in the bulk or at the surface of the oxide; (ii) Under oxygen rich conditions, or considering that there is plenty of oxygen atoms in the HfO_2 [24], such that the removed hafnium remains always in equilibrium with the oxygen gaseous, the μ_{Hf}(gas) can be obtained as $\mu_{Hf}(gas) = \mu_{HfO_2} - \mu_{O_2}$. The HfO_2 chemical potential (μ_{HfO_2}) was obtained as the energy per unit formula for the monoclinic bulk hafnium oxide, and μ_{O_2} is the energy of an isolated oxygen molecule, which was obtained through a DFT total energy calculation for an O_2 inside a cubic supercell of 15 Å side. For the silicon chemical potential, two similar limits were considered: (i) μ_{Si} as the crystalline bulk Si chemical potential, and (ii) μ_{Si} as the chemical potential of Si in SiO_2 under oxygen rich conditions, i.e., $\mu_{Si} = \mu_{SiO_2} - \mu_{O_2}$, with μ_{O_2} as above and μ_{SiO_2} obtained as the energy per unit formula of -quartz.

The results for the formation energies are presented in Fig. 1. As can be seen from Fig. 1(a), under oxygen rich conditions, the formation of a Si substitutional defect in HfO_2 is very likely to occur, specially if the Si source is the bulk crystal. Under this O-rich situation, the formation of this defect would only become unfavorable if a thick enough layer of SiO_2 would exists between the Si substrate and the HfO_2. In this Case, either the source of Si atoms would be the silica, or the Si would somehow not diffuse through this thick layer. If the SiO_2 is thin enough, such that the Si diffusion through it is significant, then the formation of a Hf silicate (at least close to the interface) seems unavoidable [25]. On the other hand, under Hf rich conditions, it is less likely that Si substitutional defects in HfO_2 will be formed.

The formation of Hf substitutional defects in SiO_2 has a behavior that is opposite to Si_{Hf}, as can be seen in Fig. 1(b), i.e., it is not likely to form under oxygen rich conditions, and becomes more probable under Hf-rich conditions. In a situation where the Si chemical potential is given by its bulk value (either thin or no SiO_2 layer), the formation of a Hf_{Si} in SiO_2 is unlikely to happen, for a large range of Hf chemical potential.

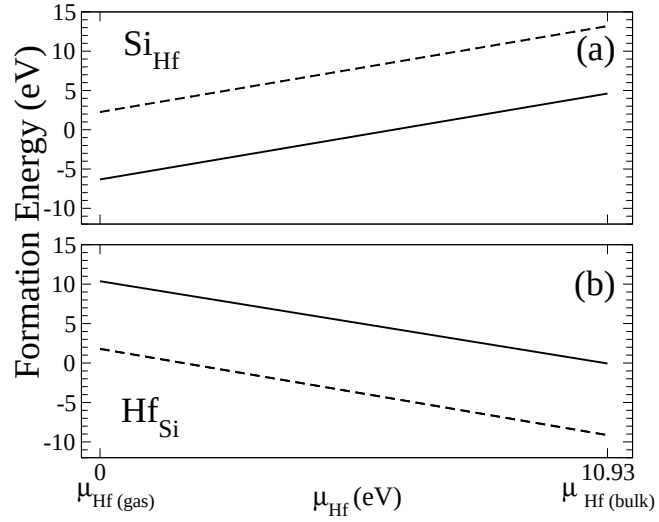

FIG. 1: Formation energies for the two substitutional defects considered in this work: (a) Si in place of a Hf in HfO_2, and (b) Hf in place of a Si in SiO_2. The formation energies are plotted as a function of the Hf chemical potential, and for two values of the Si chemical potential, the bulk Si chemical potential (solid curves) and the chemical potential for Si in the SiO_2 under an oxygen rich environment (dashed curves).

We also considered the formation of neutral oxygen vacancies (V_O), both in SiO_2 as well as in HfO_2 [21], since they can be created in films and bulk samples due to the growth cycle. The neutral oxygen vacancy in the m-HfO_2 and -quartz were generated by simple removal of an oxygen atom, followed by full relaxation of all remaining atoms. The formation energies for a V_O in XO_2 (X = Hf or Si), $E_f(V_O)$, were calculated as,

$$E_f^{XO_2}(V_O) = [E_t^{XO_2}(V_O) + \mu_O] - [E_t(XO_2)]; \quad (3)$$

where $E_t^{XO_2}(V_O)$ and $E_t(XO_2)$, are the total energies of supercells of XO_2 (X = Hf or Si) with, and without, an oxygen vacancy, respectively. The oxygen chemical potential, μ_O, was considered either as the total energy of an isolated oxygen atom, or as one half of the energy of an isolated oxygen molecule (in both cases, the O_2 triplet ground state was used). The monoclinic phase has non-equivalent oxygen atoms, i.e, which some sites are three-fold coordinated, whereas others are fourfold coordinated by hafnium atoms. In this way, we have determined the formation energy for both vacancies types using Eq. (3) and we obtain a formation energy difference around 0.02 eV. In the former case, we obtained of $E_f^{HfO_2}(V_O) = 9.32$ eV and $E_f^{SiO_2}(V_O) = 8.10$ eV, whereas for the latter choice of μ_O, we obtained $E_f^{HfO_2}(V_O) = 6.38$ eV

and $E_f^{SiO_2}(V_O) = 5.16$ eV. This indicates that, although neutral oxygen vacancies are energetically unfavorable in both materials, they are more stable in silicon oxide than in hafnium oxide, by approximately 1.23 eV. This implies that, if an oxygen deficient HfO_2 is grown on top of a SiO_2 layer, oxygen atoms will migrate from SiO_2. In this way, oxygen vacancies are created in the silica layer toward the HfO_2, healing at the sometimes oxygen vacancies in the hafnia. Indications that this process does indeed occur, has been recently reported [13].

In summary, our results show that, unless the hafnium chemical potential is always very close to its bulk value, i.e., oxygen-poor growth conditions, the formation of Si substitutional defects in the HfO_2 is almost unavoidable. This will lead to the formation of a silicate-like layer close to the Interface. For a very large range of Hf chemical potential it is very likely that incoming silicon atoms from the Si substrate will form a $(HfO_2)_x(SiO_2)_y$ layer, as supported by experimental observations [25]. The only way to prevent the formation of a silicate layer would be through the use of an oxygen deficient HfO_2, as has been observed [13]. However, even if this silicate formation is prevented in the initial steps of dielectric growth, it seems almost impossible that it will not be formed given the necessary further thermal processing steps, unless a barrier for the Si diffusion being introduced [9].

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